## SK12 THRU SK16

SURFACE MOUNT SCHOTTKY BARRIER RECTIFIER

TECHNICAL SPECIFICATION

## VOLTAGE: 20 TO 60V CURRENT: 1.0A

## FEATURES

- Ideal for surface mount pick and place application
- Low profile package
- Low power loss, high efficiency
- High current capability,low $\mathrm{V}_{\mathrm{F}}$
- High surge capability
- Open junction chip,silastic passivated
- High temperature soldering guaranteed:
$260^{\circ} \mathrm{C} / 10 \mathrm{sec} /$ at terminal


## MECHANICAL DATA

- Terminal: Plated leads solderable per MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O recognized flame retardant epoxy
- Polarity: Color band denotes cathode



## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60 Hz , resistive or inductive load rating at $25^{\circ} \mathrm{C}$, unless otherwise stated, for capacitive load, derate current by $20 \%$ )

| RATINGS | SYMBOL | SK12 | SK13 | SK14 | SK15 | SK16 | UNITS |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Maximum Repetitive Peak Reverse Voltage | $\mathrm{V}_{\text {RRM }}$ | 20 | 30 | 40 | 50 | 60 | V |
| Maximum RMS Voltage | $\mathrm{V}_{\text {RMS }}$ | 14 | 21 | 28 | 35 | 42 | V |
| Maximum DC Blocking Voltage | $V_{D C}$ | 20 | 30 | 40 | 50 | 60 | V |
| Maximum Average Forward Rectified Current $\left(\mathrm{T}_{\mathrm{L}}=110^{\circ} \mathrm{C}\right)$ | $\mathrm{I}_{\text {(AV) }}$ | 1.0 |  |  |  |  | A |
| Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load) | $\mathrm{I}_{\text {FSM }}$ | 30 |  |  |  |  | A |
| Maximum Instantaneous Forward Voltage (at rated forward current) | $V_{F}$ | 0.5 |  |  | 0.7 |  | $V$ |
| Maximum DC Reverse Current $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$ <br> (at rated DC blocking voltage) $\mathrm{T}_{\mathrm{a}}=100^{\circ} \mathrm{C}$ | $I_{\text {R }}$ | $\begin{gathered} \hline 0.5 \\ 10.0 \end{gathered}$ |  |  |  |  | $\begin{aligned} & \mathrm{mA} \\ & \mathrm{~mA} \end{aligned}$ |
| Typical Junction Capacitance (Note 1) | $\mathrm{C}_{J}$ | 110 |  |  |  |  | pF |
| Typical Thermal Resistance (Note 2) | $\mathrm{R}_{8}(\mathrm{ja})$ | 20 |  |  |  |  | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Storage and Operation Junction Temperature | $\mathrm{T}_{\text {STG }}, \mathrm{T}_{\mathrm{J}}$ | -65 to +150 |  |  |  |  | ${ }^{\circ} \mathrm{C}$ |

Note:

1. Measured at 1.0 MHz and applied voltage of $4.0 \mathrm{~V}_{\mathrm{dc}}$
2.Thermal resistance from junction to terminal mounted on $5 \times 5 \mathrm{~mm}$ copper pad area
http://www.sse-diode.com
